

TO-263-2L Plastic-Encapsulate MOSFETS

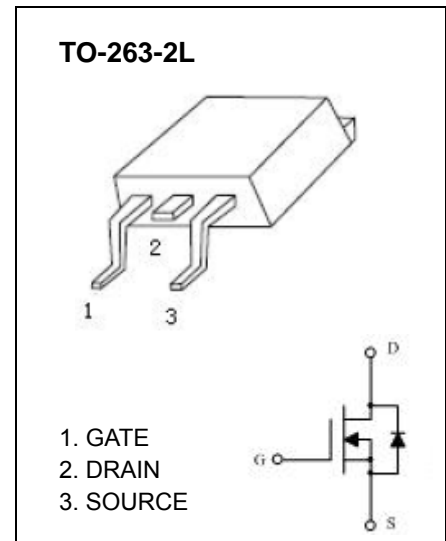
CJB08N65 N-Channel Power MOSFET

GENERAL DESCRIPTION

This advanced high voltage MOSFET is designed to stand high energy in the avalanche mode and switch efficiently. This new high energy device also offers a drain-to-source diode fast recovery time. Designed for high voltage, high speed switching applications such as power supplies, converters, power motor controls and bridge circuits.

FEATURE

- High Current Rating
- Lower $R_{DS(on)}$
- Lower Capacitance
- Lower Total Gate Charge
- Tighter V_{SD} Specifications
- Avalanche Energy Specified



Maximum ratings ($T_a=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	650	V
Gate-Source Voltage	V_{GS}	± 30	
Continuous Drain Current	I_D	8	A
Pulsed Drain Current	I_{DM}	32	
Single Pulsed Avalanche Energy (note1)	E_{AS}	250	mJ
Thermal Resistance from Junction to Ambient	$R_{\theta JA}$	62.5	$^\circ\text{C}/\text{W}$
Operating and Storage Temperature Range	T_J, T_{STG}	-55 ~ +150	$^\circ\text{C}$
Maximum Lead Temperature for Soldering Purposes , Duration for 5 Seconds	T_L	260	

Electrical characteristics (T_a=25°C unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Off characteristics						
Drain-source breakdown voltage	V _{(BR)DSS}	V _{GS} = 0V, I _D =250μA	650			V
Drain-source diode forward voltage	V _{SD}	V _{GS} = 0V, I _S =8A			1.4	
Zero gate voltage drain current	I _{DSS}	V _{DS} =650V, V _{GS} =0V			10	μA
Gate-body leakage current	I _{GSS}	V _{DS} =0V, V _{GS} = ±30V			±100	nA
On characteristics (note2)						
Gate-threshold voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250μA	2.0		4.0	V
Static drain-source on-resistance	R _{DS(on)}	V _{GS} =10V, I _D =4A		1.0	1.4	Ω
Forward transconductance	g _{fs}	V _{DS} =50V, I _D =3.9A		8.5		S
Dynamic characteristics (note 3)						
Input capacitance	C _{iss}	V _{DS} =25V, V _{GS} =0V, f =1MHz			1255	pF
Output capacitance	C _{oss}				135	
Reverse transfer capacitance	C _{rss}				16	
Switching characteristics (note 3)						
Total gate charge	Q _g	V _{DS} =520V, V _{GS} =10V, I _D =8A		28	36	nC
Gate-source charge	Q _{gs}			4.5		
Gate-drain charge	Q _{gd}			12		
Turn-on delay time	t _{d(on)}	V _{DD} =325V, R _G =25Ω, I _D =8A			45	ns
Turn-on rise time	t _r				130	
Turn-off delay time	t _{d(off)}				170	
Turn-off fall time	t _f				140	

Notes :

- L=7mH, I_L=8A, V_{DD}=50V, R_G=25Ω, Starting T_J=25°C.
- Pulse Test: Pulse width≤300μs, duty cycle ≤2%.
- These parameters have no way to verify.